Supplementary Information

Inverse design of semiconductor materials with deep generative models

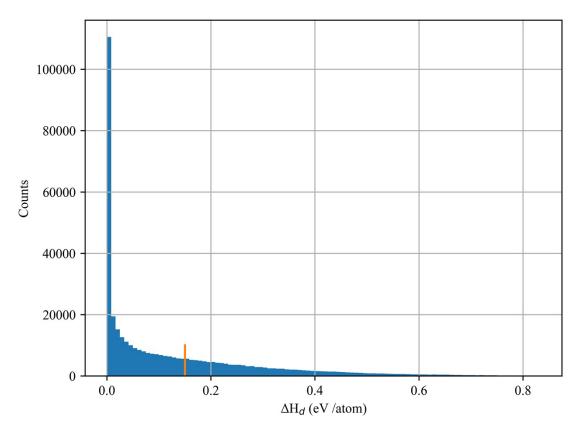


Fig. S1. Histogram of the distribution of decomposition enthalpy (ΔH_d) for the entire dataset. Approximately 2/3 of the samples in the dataset have a ΔH_d less than or equal to 0.15 eV/atom.

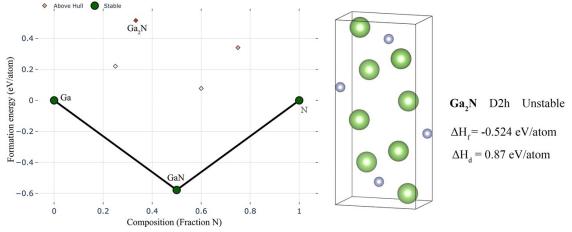


Fig. S2. The binary convex hull phase diagram for Ga-N systems incorporates the energies of Ga-N compositions from the dataset as well as the energy of Ga_2N predicted by VGD-CG.

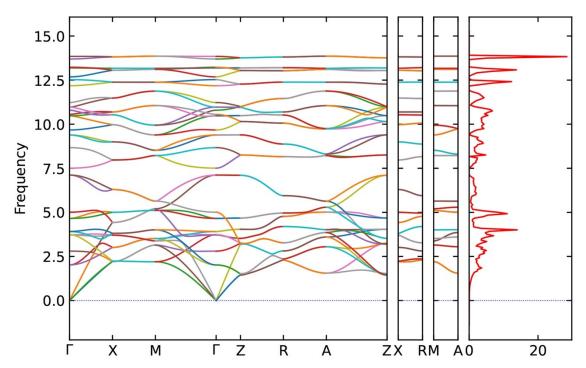


Fig. S3. The phonon dispersion curves calculated by PBE along symmetry lines in the Brillouin zone for Si₃Ge₂.

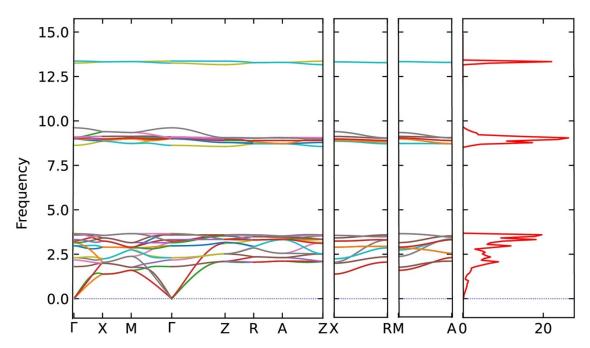


Fig. S4. The phonon dispersion curves calculated by PBE along symmetry lines in the Brillouin zone for VBi₃O₇.

Table S1. The setup of model hyperparameters used in VAE, GAN and DDPM.

Parameters	VAE	GAN	DDPM
z_dim	128	128	\
w_kl	0.01	\	١
batch_size	5120	5120	256
epochs	20	20	20
lr	0.001	0.001	0.0001
optimizer	Adam	Adam	Adam
train_ratio	0.9	0.9	0.9
test_ratio	0.1	0.1	0.1
n_critic	\	5	١
lambda_penalty	\	10	١
beta_end	\	\	0.02
timesteps	\	\	500
beta_start	\	\	0.0001
schedule_name	\	\	linear_beta_schedule